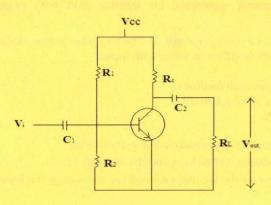


7. For the CE transistor amplifier circuit given in the figure below,  $V_{CC}$  =20  $\dot{V}$ ,  $R_{C}$ =20  $K\Omega$ ,  $R_{L}$  = 2  $M\Omega$ ,  $R_{I}$ = 10  $K\Omega$ ,  $R_{2}$  = 10  $K\Omega$ ,  $\beta$  = 100. Find the  $r_{e}$  model and (i)  $R_{in}$  (ii)  $R_{L}$  (iii)  $A_{i}$  (iv)  $A_{v}$  (v)  $A_{p}$  &  $G_{p}$ 



8. Derive the relation of frequency of oscillation and the feedback attenuation required for sustained oscillations for a Colpitt's oscillator.

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REV-00 MSE/05/10 2018/06

## M.Sc. ELECTRONICS SECOND SEMESTER IC TECHNOLOGY & ANALOG ELECTRONIC CIRCUITS

MSE - 203

(Use Separate Answer Scripts for Objective & Descriptive)

Duration: 3 hrs.

Full Marks: 70

PART-A: Objective

Time: 20 min.

Marks: 20

Choose the correct answer from the following:

 $1 \times 20 = 20$ 

1. An amplifier has a power gain of 200. What is its gain in dB?

a. 14 dB

b.23 dB

c. 22 dB

d. 17 dB

2. What are the types of MOSFET devices available?

a. P-type enhancement type MOSFET

b. N-type enhancement type MOSFET

c. Depletion type MOSFET

d. All of the mentioned

3. Which is the most striking feature in monolithic integrated circuit transistor?

a. Collector contact is present at the bottom of IC

b. Collector contact is present at the top of IC

c. Collector contact is absent

d. Collector contact is present on one of the sides of IC

**4.** Which of the following is used to obtain silicon crystal structure while fabricating Integrating Circuits?

a. Oxidation

b. Epitaxial growth

c. Photolithography

d. Silicon wafer preparations

5. Why oxidation process is required?

a. To protect against contamination

b. To use it for fabrication various components

c. To prevent diffusion of impurities

d. All of the mentioned

6. Where does the operating point of a Class A power amplifier lie?

a. At the middle of ac load line

b. Approximately at collector cut-off on both the dc and ac load lines

c. Inside the collector cut-off region on ac load line

d. At the middle of dc load line

7. The active components of the IC's are formed in

a. Substrate

b. Sio2 layer

c. Epitaxial layer

d. None of these

8. Ultraviolet radiation is used in IC fabrication for

a. Diffusion

b. Masking

c. Isolation

d. Etching

== \*\*\* = =

9.	The Barkhausen criterion for sustained osci <b>a.</b> $A\beta=1$ <b>c.</b> $ A\beta <1$	llations is given by  b. $ A\beta  \ge 1$ d. $\angle A\beta = 180^{\circ}$
10.	Which of the following configuration is used a. Common base configuration c. Common collector configuration	
11.	Which of the following amplifier class have a. Class A c. Class C	highest linearity and lowest distortion? b. Class B d. Class B push-pull
12.	Which of the following class have a theoretic a. Class A b.Class C c. C	cal efficiency of 78.5%? Class B d. Class D
13.	Oscillators are used to AC voltage.  a. Prevent c. Amplify	b. Generate d. Rectify
14.	Negative resistance are incorporated in oscil a. Sustained oscillation c. Biasing the oscillator	lator for b. Damped oscillation d. Increasing amplitude of oscillation
15.	In an oscillator if phase of feedback is same a feedback is called  a. Positive feedback  c. Cannot be predicted	b. Negative feedback d. Either positive or negative depending upon frequency
16.	Oscillation can be classified as damped and a. Input power c. Amplitude	
17.	Amplifier gain for RC phase shift oscillation minimum of a. 43 b. 4	, to obey Barkhausen's criteria should be c. 10 d. 29
18.	If L1 and L2 are the inductances used in Har equation of frequency calculation is equal to a. (L1×L2)/(L1+L2) c. L1+L2	
19.	The parameter $h_{ie}$ stands for input impedance a. CB arrangement with output shorted c. CE arrangement with output shorted	
20.	In an RC phase shift oscillator, the minimu in cascade will be	
	a. 1 b. 2	c. 3 d. 4

## PART-B: Descriptive

Time: 2 hrs. 40 min. Marks: 50

## [ Answer question no.1 & any four (4) from the rest ]

- 1. Define an integrated circuit. What are the basic processes involved in 10 fabricating ICs?
- 2. a. Derive the general expression for transfer gain with negative 5+5=10feedback.
  - b. An amplifier has a voltage gain of 10. The amplifier is now modified to provide a 40% feedback in series with input. Calculate
    - i. voltage gain with feedback;
    - ii. amount of feedback in dB;
    - iii. Loop gain.
- 3. a. Why positive resist is preferred over negative resist?

2+3+5 b. Distinguish between wet etching and dry etching. =10

c. Explain any one of the techniques used for measuring thickness of thin film.

- 4. a. Describe the operation of complementary symmetry push-pull Class 5+5=10B amplifier with suitable diagram.
  - b. Show that the maximum efficiency of Class A power amplifier is 25%
- 5. a. A CE transistor amplifier is characterized by  $h_{ie}=4$  K $\Omega$ ,  $h_{re}=4$ X  $10^{-4}$ , 5+5=10 $h_{fe}=100$  and  $h_{oe}=4X10^{-6}$  A/V. If load resistance is 8 K $\Omega$  and source resistance is 200  $\Omega$ , determine  $Z_{in}$ ,  $Z_{out}$ ,  $A_v$  and  $A_i$ .
  - **b.** Determine the h-parameters of the circuit:

